

**Maximum Ratings** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	-40	V
Gate-Source Voltage			$V_{GSS}$	$\pm 20$	
Continuous Drain Current	$V_{GS} = -10\text{V}$	(Notes 6)	$I_D$	-8.0	A
		$T_A = 70^\circ\text{C}$ (Notes 6)		-6.9	
		(Notes 5)		-6.0	
Pulsed Drain Current	$V_{GS} = -10\text{V}$	(Notes 7)	$I_{DM}$	-30	
Continuous Source Current (Body diode)			(Notes 7)	$I_S$	
Pulsed Source Current (Body diode)			(Notes 7)	$I_{SM}$	-30

**Thermal Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic			Symbol	Value	Unit
Power Dissipation	(Notes 5)	$P_D$		1.52	W
	(Notes 6)			2.4	
Thermal Resistance, Junction to Ambient	(Notes 5)	$R_{\theta JA}$		82	$^\circ\text{C/W}$
	(Notes 6)			52	
Thermal Resistance, Junction to Lead	(Notes 8)	$R_{\theta JL}$		48.85	
Operating and Storage Temperature Range			$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

- Notes:
5. For a device surface mounted on minimum recommended FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  6. Same as note (2), except the device is surface mounted on 25mm X 25mm X 1.6mm FR4 PCB.
  7. Repetitive rating on 25mm X 25mm FR4 PCB,  $D=0.02$ , pulse width 300 $\mu\text{s}$  – pulse width by maximum junction temperature.
  8. Thermal resistance from junction to solder-point (at the end of the drain lead).

**Thermal Characteristics**

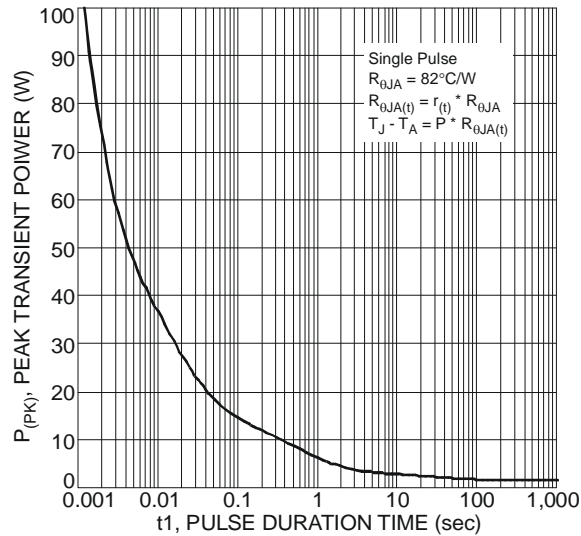


Fig. 1 Single Pulse Maximum Power Dissipation

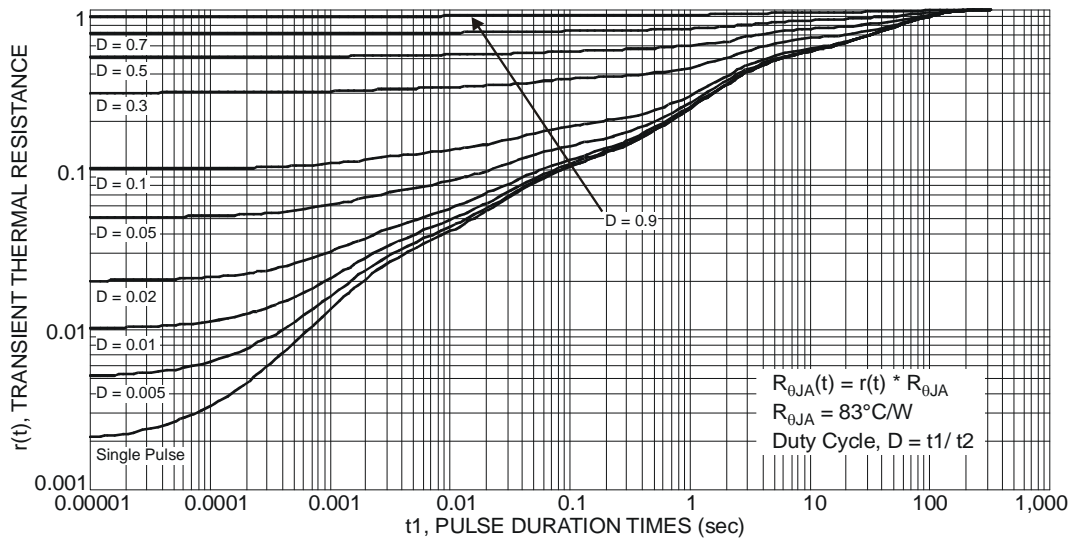


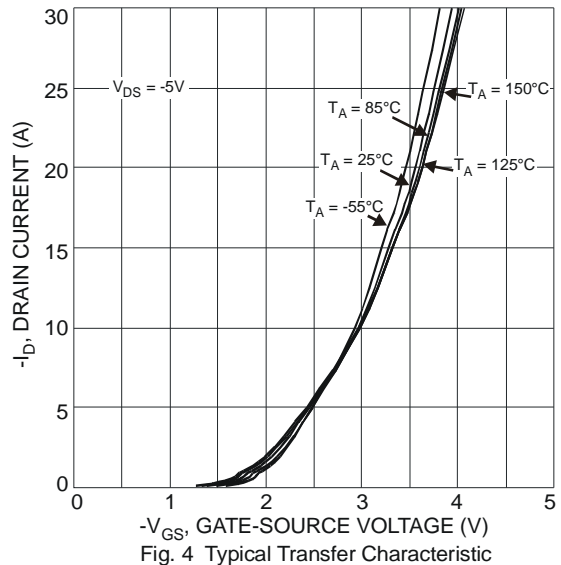
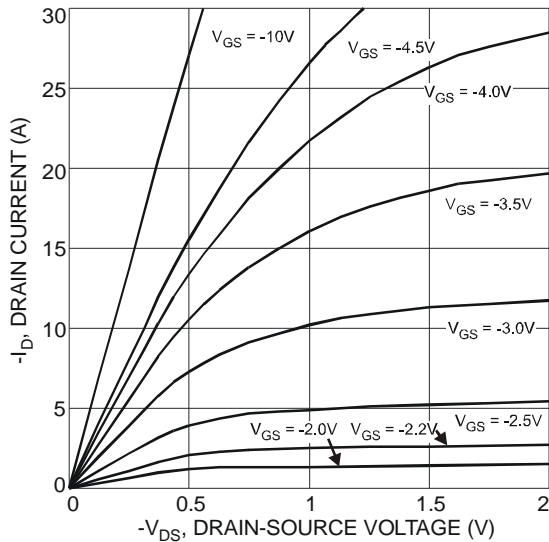
Fig. 2 Transient Thermal Resistance

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-40	—	—	V	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	-1.0	$\mu\text{A}$	$V_{DS} = -40\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(th)}$	-0.8	-1.3	-1.8	V	$I_D = -250\mu\text{A}, V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 9)	$R_{DS(ON)}$	—	18	25	m $\Omega$	$V_{GS} = -10\text{V}, I_D = -3\text{A}$
			30	45		$V_{GS} = -4.5\text{V}, I_D = -3\text{A}$
Forward Transconductance (Notes 9 & 10)	$g_{fs}$	—	16.6	—	S	$V_{DS} = -5\text{V}, I_D = -3\text{A}$
Diode Forward Voltage (Note 9)	$V_{SD}$	—	-0.7	-1.0	V	$I_S = -1\text{A}, V_{GS} = 0\text{V}$
<b>DYNAMIC CHARACTERISTICS (Note 10)</b>						
Input Capacitance	$C_{iss}$	—	1640	—	pF	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	$C_{oss}$	—	179	—		
Reverse Transfer Capacitance	$C_{rss}$	—	128	—		
Gate Resistance	$R_g$	—	6.43	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge (Note 11)	$Q_g$	—	14.0	—	nC	$V_{GS} = -4.5\text{V}$ $V_{DS} = -20\text{V}$ $I_D = -3\text{A}$
Total Gate Charge (Note 11)	$Q_{g1}$	—	33.7	—		
Gate-Source Charge (Note 11)	$Q_{gs}$	—	5.5	—		
Gate-Drain Charge (Note 11)	$Q_{gd}$	—	7.3	—		
Turn-On Delay Time (Note 11)	$t_{D(on)}$	—	6.9	—	ns	$V_{DD} = -20\text{V}, V_{GS} = -10\text{V}$ $I_D = -3\text{A}$
Turn-On Rise Time (Note 11)	$t_r$	—	14.7	—		
Turn-Off Delay Time (Note 11)	$t_{D(off)}$	—	53.7	—		
Turn-Off Fall Time (Note 11)	$t_f$	—	30.9	—		

Notes: 9. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$   
 10. For design aid only, not subject to production testing.  
 11. Switching characteristics are independent of operating junction temperatures.

**Typical Characteristics**



**DMP4025LSS**

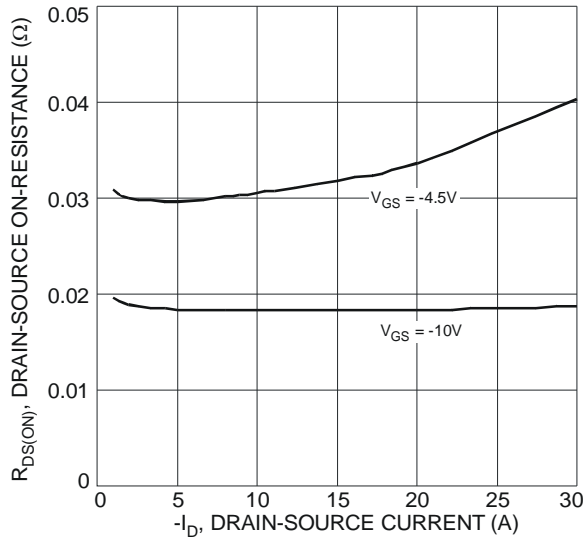


Fig. 5 Typical On-Resistance vs. Drain Current and Gate Voltage

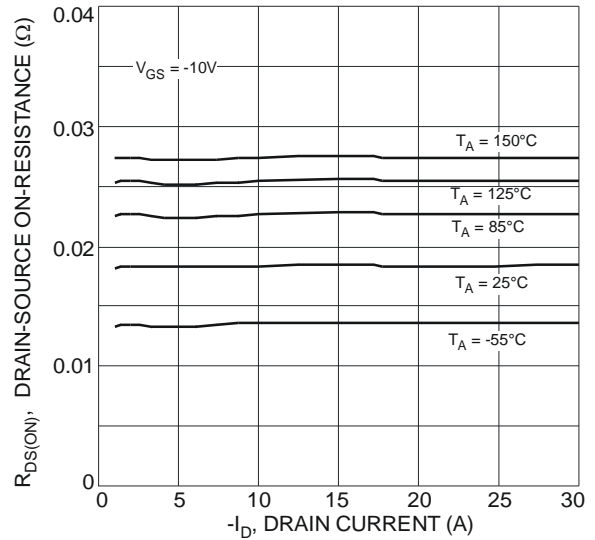


Fig. 6 Typical On-Resistance vs. Drain Current and Temperature

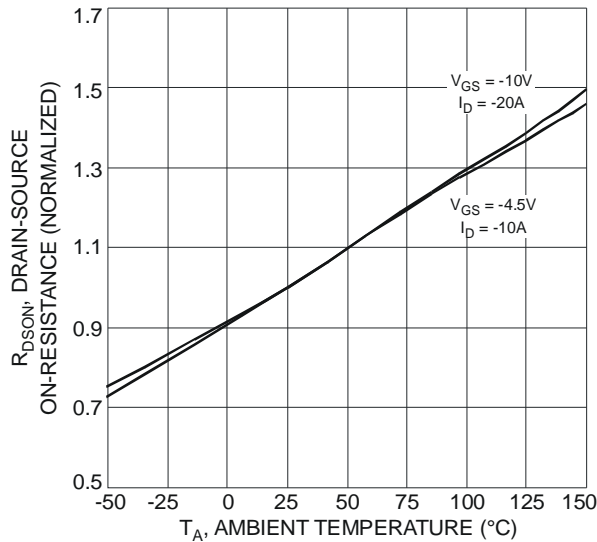


Fig. 7 On-Resistance Variation with Temperature

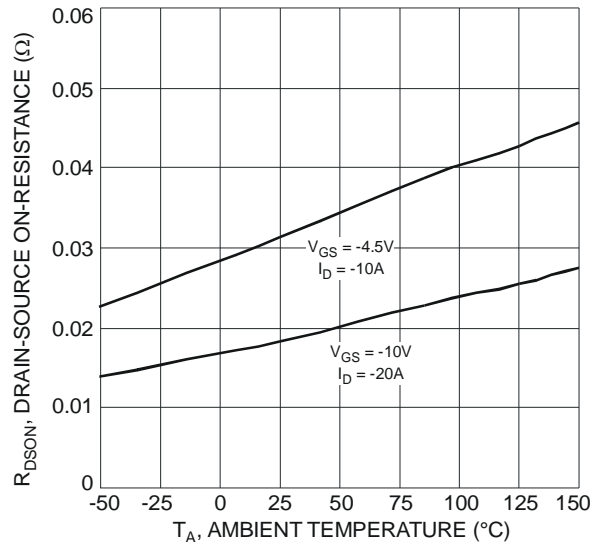


Fig. 8 On-Resistance Variation with Temperature

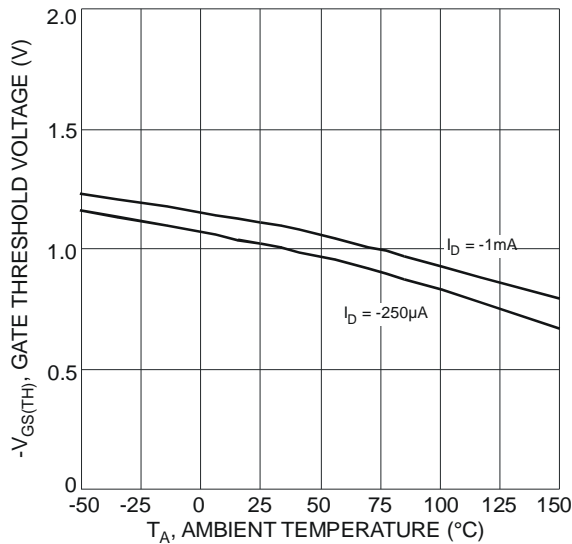


Fig. 9 Gate Threshold Variation vs. Ambient Temperature

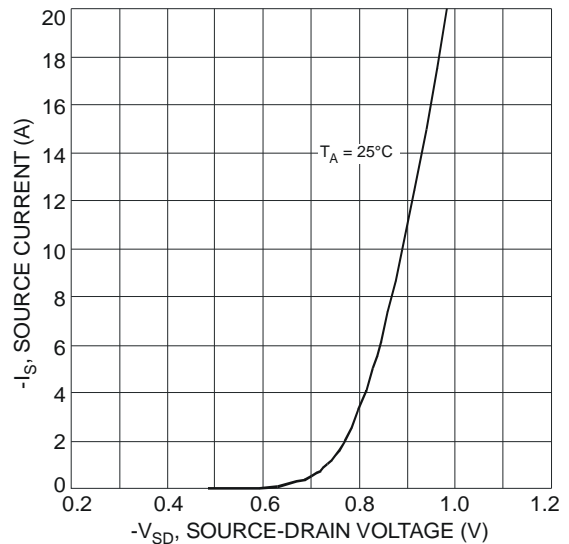
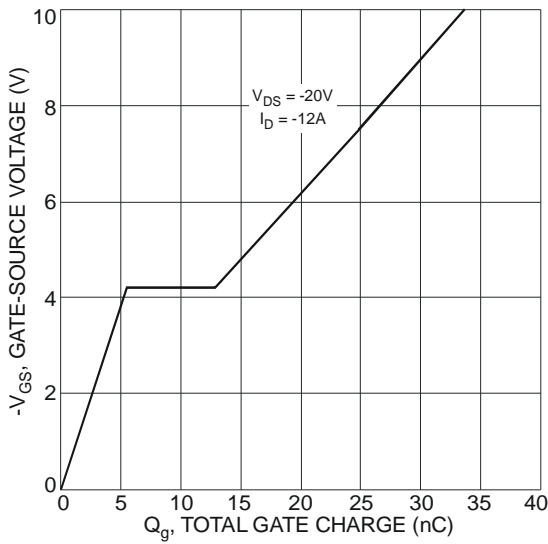
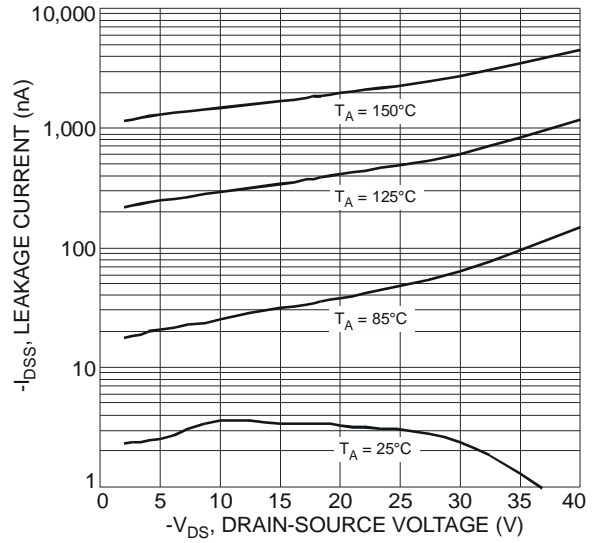
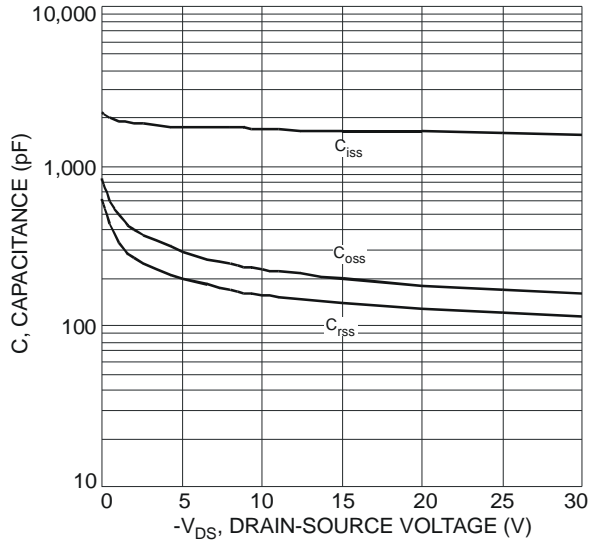
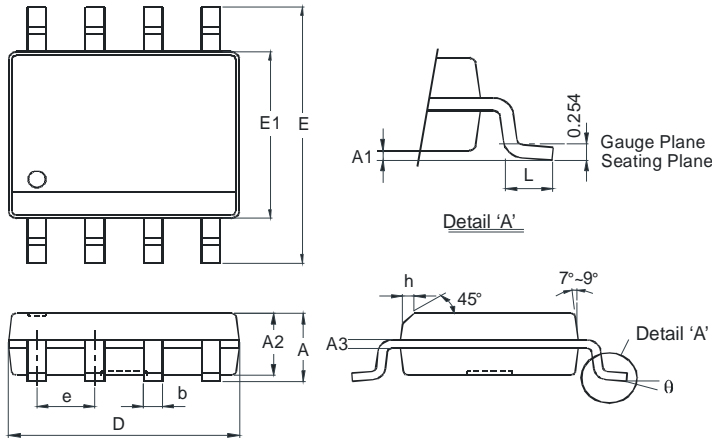


Fig. 10 Diode Forward Voltage vs. Current

**DMP4025LSS**

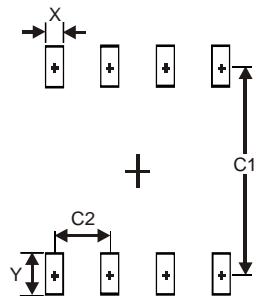


**Package Outline Dimensions**



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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